

● PRINTER RUSH ●

(PTO ASSISTANCE)

Application : <u>10/684,424</u>	Examiner : <u>Huynh</u>	GAU : <u>28/8</u>
From: <u>DP</u>	Location: <u>IDC</u> FMF FDC	Date: <u>12/5/2005</u>

Tracking #: EPM 10/684,424 Week Date: 8/15/2005

DOC CODE	DOC DATE	MISCELLANEOUS
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<input checked="" type="checkbox"/> SPEC	<u>7/25/2005</u>	

[RUSH] MESSAGE: Amendment to the Specification: In the Abstracts Replace the original Abstract with the Amended Abstract, but there is no Abstract on the separate sheet. to Amend, please provide.

Thanks.

[XRUSH] RESPONSE: _____

See misc comm

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INITIALS: [Signature]

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Fax no. 703-308-6642 Phone no. 703-746-6830

From Mitchell W. Shapiro Phone no. 703.610.8652

Date January 19, 2006 Time _____

Your Ref.: 10/684,424;
File no. Our Ref.: XA-9945 Pages including cover 6

Message

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XA-9945

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Tomoyuki ISHII et al.

Conf. No.: 3924

Appln. No.: 10/684,424

Group Art Unit: 2818

Filed: October 15, 2003

Examiner: A. Huynh

For: SEMICONDUCTOR MEMORY DEVICE

* * *

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS*Mail Stop Issue Fee*

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Sir:

In response to the Notice (copy enclosed) mailed December 20, 2005, the amended abstract is transmitted herewith. Also transmitted herewith, in case is needed, is a marked-up version of the original abstract showing the amendments.

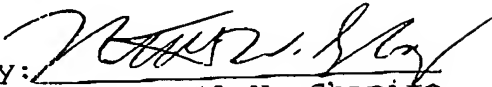
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such extension is hereby requested.

Respectfully submitted,

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January 19, 2006

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10684424

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12/20/05

NOTICE TO FILE CORRECTED APPLICATION PAPERS***Notice of Allowance Mailed***

This application has been accorded an Allowance Date and is being prepared for issuance. The application, however, is incomplete for the reasons below.

Applicant is given 30 days from the mail date of this Notice within which to correct the informalities indicated below. A failure to reply will result in the application being ABANDONED. This period for reply is NOT extendable under 37 CFR 1.136 (a) or (b).

- ♦ Amended abstract is missing from application. Fax missing information to number below.

APPLICANT MUST SUPPLY MISSING INFORMATION WITHIN 30 DAYS OF THE MAIL DATE OF THIS NOTICE.

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A handwritten signature in black ink, appearing to read "Rori Burch", written over a horizontal line.

Rori Burch
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703-305-0333 exL135 (V)

ABSTRACT OF THE DISCLOSURE

To realize a semiconductor memory device with reduced cell-to-cell variation in writing characteristics a semiconductor memory has a source region and a drain region, which are formed parallel to each other, and an assist electrode which is between and parallel to the source and drain regions without overlapping, so that at the time of writing, the assist electrode is used as an assist electrode for hot electrons to be injected at the source side and at the time of reading, an inversion layer formed under the assist electrode is used as the source region or the drain region.

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ABSTRACT OF THE DISCLOSURE

~~Flash memory is rapidly decreasing in price. There is a demand for a new memory system that permits size reduction and suits multiple value memory. A flash memory of AND type suitable for multiple value memory with multiple level threshold values can be made small in area if the inversion layer is utilized as the wiring, however, it suffers the disadvantage of greatly varying in writing characteristics from cell to cell. Another promising method of realizing multiple value memory is to change the storage locations. This method, however, poses a problem with disturbance at the time of operation. The present invention provides one way to.~~ To realize a semiconductor memory device with reduced cell-to-cell variation in writing characteristics, The a semiconductor memory has a source region and a drain region, which are formed parallel to each other, and an assist electrode which is between and parallel to the source and drain regions without overlapping, so that ~~it uses,~~ at the time of writing, the assist electrode is used as the an assist electrode for hot electrons to be injected at the source side and ~~it uses,~~ at the time of reading, the an inversion layer formed under the assist electrode is used as the source region or the drain region.

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